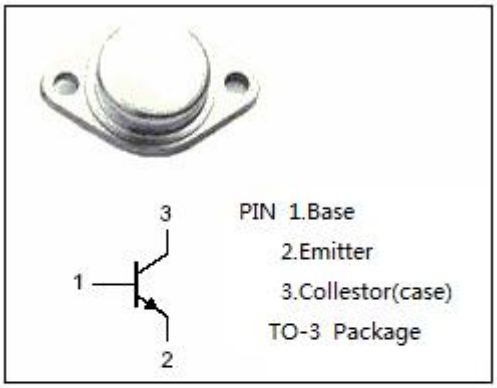
isc Silicon NPN Power Transistor — BU204

DESCRIPTION

- High Voltage-V_{CEX}= 1300V(Min.)
- Collector Current- I_C = 2.5A
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

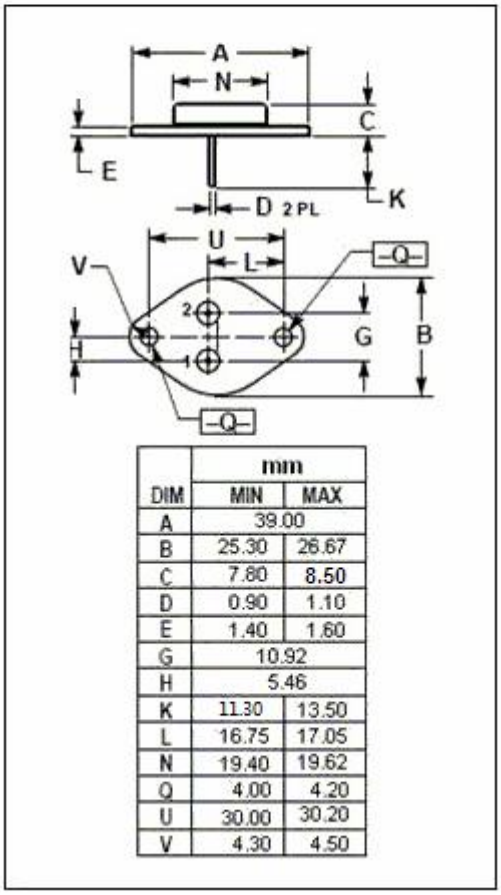


APPLICATIONS

- Designed for use in large screen color deflection circuits .

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CEX}	Collector-Emitter Voltage	1300	V
V_{CEO}	Collector-Emitter Voltage	600	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current-Continuous	2.5	A
I_{CM}	Collector Current-Peak	3.0	A
I_B	Base Current-Continuous	1.0	A
P_C	Collector Power Dissipation @T_C=25℃	36	W
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature	-65~150	℃



DIM	mm MIN	MAX
A	39.00	
B	25.30	26.67
C	7.80	8.50
D	0.90	1.10
E	1.40	1.60
G	10.92	
H	5.46	
K	11.30	13.50
L	16.75	17.05
N	19.40	19.62
Q	4.00	4.20
U	30.00	30.20
V	4.30	4.50

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j\text{-}c}$	Thermal Resistance,Junction to Case	2.5	℃/W

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEO(SUS)}$	Collector-Emitter Sustaining Voltage	I_C= 50mA, I_B= 0	600			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= 2A; I_B= 1A			5.0	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	I_C= 2A; I_B= 1A			1.5	V
I_{CES}	Collector Cutoff Current	V_{CE}= 1300V; V_{BE}= 0			1.0	mA
I_{EBO}	Emitter Cutoff Current	V_{EB}= 5.0V ; I_C= 0			10	mA
h_{FE}	DC Current Gain	I_C= 2A ; V_{CE}= 5V	2			
C_{OB}	Output Capacitance	I_E= 0; V_{CB}= 10V; f_{test}= 1MHz		50		pF
f_T	Current-Gain—Bandwidth Product	I_C= 0.1A; V_{CE}= 5V; f_{test}= 1MHz		4		MHz
t_f	Fall Time	I_C= 2A; I_B= 1A; L_B= 25 μ H		0.65		μ s